TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π−MOSV)

2SK2836

Chopper Regulator, DC−DC Converter and Motor Drive Applications

- Low drain−source ON resistance : $R_{DS\ (ON)}$ = 6.4 Ω (typ.)
- High forward transfer admittance : $|Y_{fs}|$ = 0.85 S (typ.)
- Low leakage current : I_{DSS} = 100 μA (max) (V_{DSS} = 600 V)
- Enhancement−mode : V_{th} = 2.0~4.0 V (V_{DS} = 10 V, I_D = 1 mA)

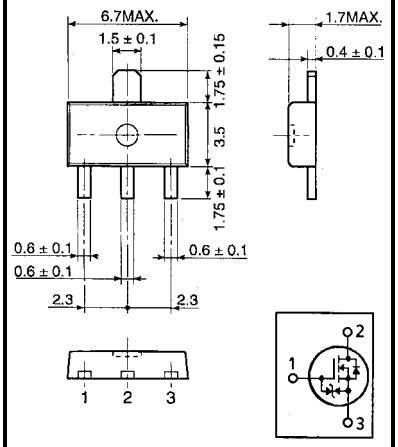
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain−source voltage		V_{DSS}	600	V
Drain−gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	600	V
Gate−source voltage		V_{GSS}	±30	V
Drain current	DC (Note 1)	I_D	1	A
	Pulse (Note 1)	I_{DP}	2	A
Drain power dissipation (Note 2)		P_D	2.5	W
Single pulse avalanche energy (Note 3)		E_{AS}	56	mJ
Avalanche current		I_{AR}	1	A
Repetitive avalanche energy (Note 4)		E_{AR}	0.25	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	50	°C / W

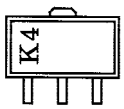
Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-7H1B

Weight: 0.12 g (typ.)

Marking



Note 1: Please use devices on condition that the channel temperature is below 150°C.

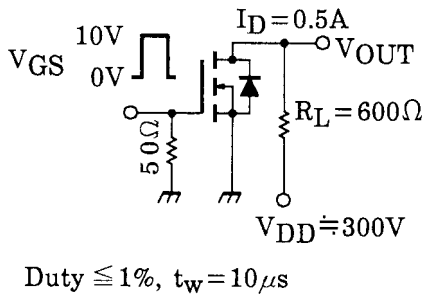
Note 2: Mounted on ceramic substrate (25.4 mm × 25.4 mm × 0.8 mm)

Note 3: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 100 mH, R_G = 25 Ω, I_{AR} = 1 A

Note 4: Repetitive rating; Pulse width limited by maximum channel temperature.

This transistor is an electrostatic sensitive device.
Please handle with caution.

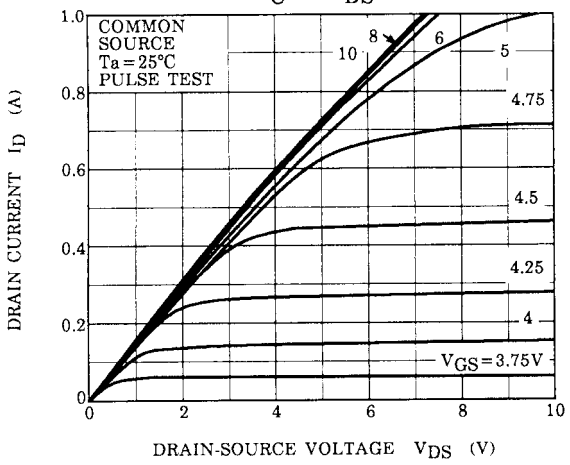
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±25 V, V_{DS} = 0 V	—	—	±10	μA
Gate−source breakdown voltage		$V_{(BR)\ GSS}$	I_G = ±10μA, V_{DS} = 0 V	±30	—	—	V
Drain cut−off current		I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V	—	—	100	μA
Drain−source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	600	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	2.0	—	4.0	V
Drain−source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 10 V, I_D = 0.5 A	—	6.4	9.0	Ω
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 0.5 A	0.4	0.85	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	190	—	pF
Reverse transfer capacitance		C_{rss}		—	15	—	
Output capacitance		C_{oss}		—	55	—	
Switching time	Rise time	t_r		—	12	—	ns
	Turn−on time	t_{on}		—	55	—	
	Fall time	t_f		—	40	—	
	Turn−off time	t_{off}		—	90	—	
Total gate charge (gate−source plus gate−drain)		Q_g	V_{DD} ≈ 400 V, V_{GS} = 10 V, I_D = 1 A	—	9	—	nC
Gate−source charge		Q_{gs}		—	3.5	—	
Gate−drain (“miller”) Charge		Q_{gd}		—	5.5	—	

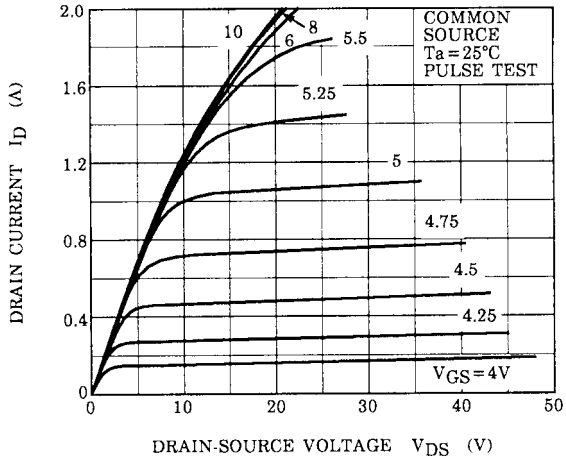
Source−Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	1	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	2	A
Forward voltage (diode)	V_{DSF}	I_{DR} = 1 A, V_{GS} = 0 V	—	—	−1.7	V
Reverse recovery time	t_{rr}	I_{DR} = 1 A, V_{GS} = 0 V, dI_{DR} / dt = 100 A / μs	—	400	—	ns
Reverse recovery charge	Q_{rr}		—	1.4	—	μC

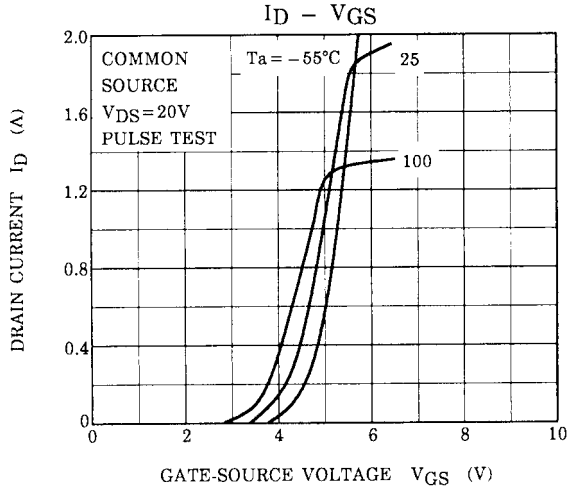
I_C – V_{DS}



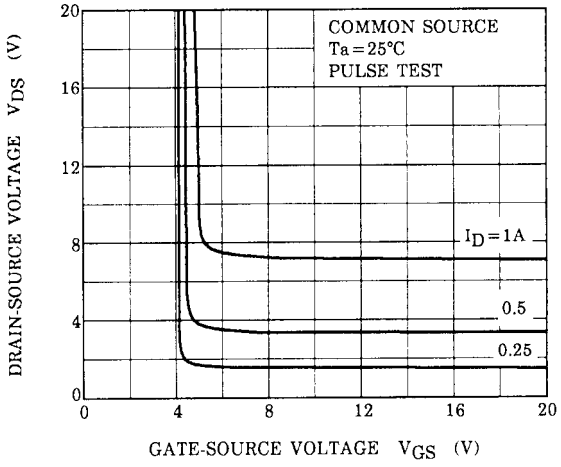
I_D – V_{DS}



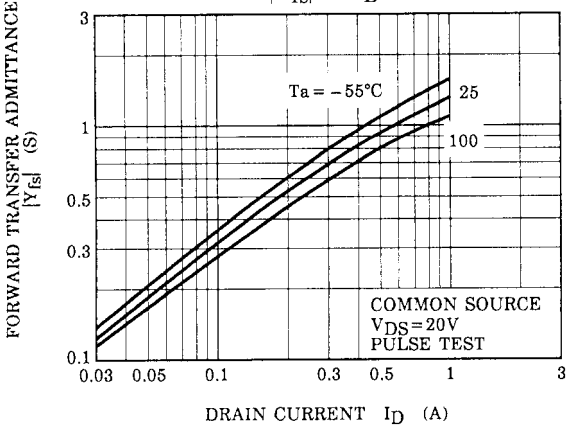
I_D – V_{GS}



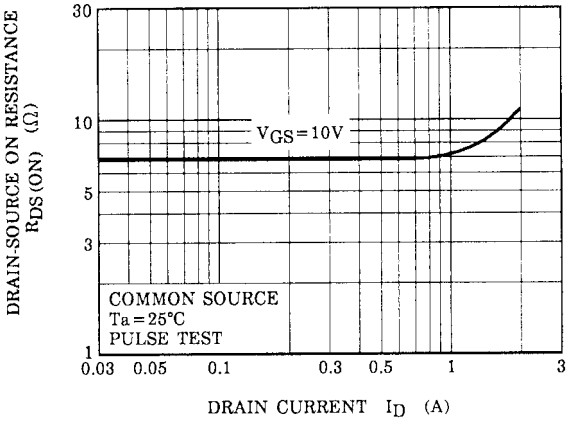
V_{DS} – V_{GS}



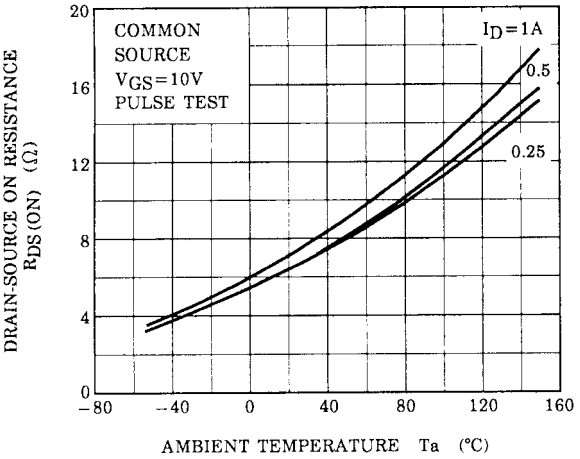
$|Y_{fs}|$ – I_D



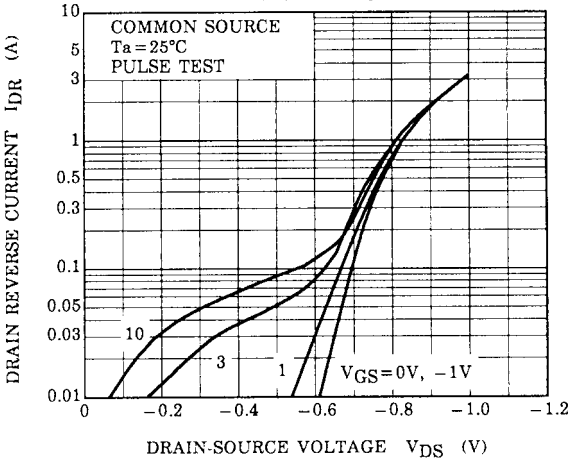
$R_{DS(ON)}$ – I_D



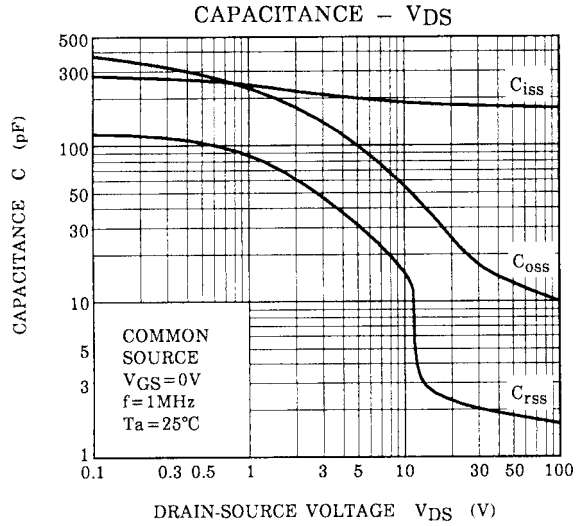
$R_{DS\,(ON)}$ – Ta



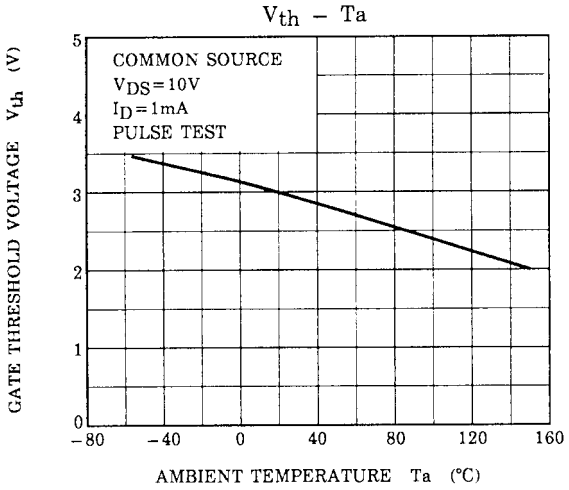
I_{DR} – V_{DS}



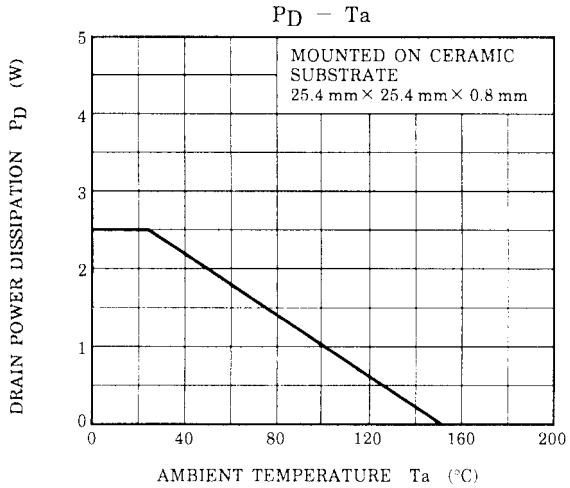
CAPACITANCE – V_{DS}



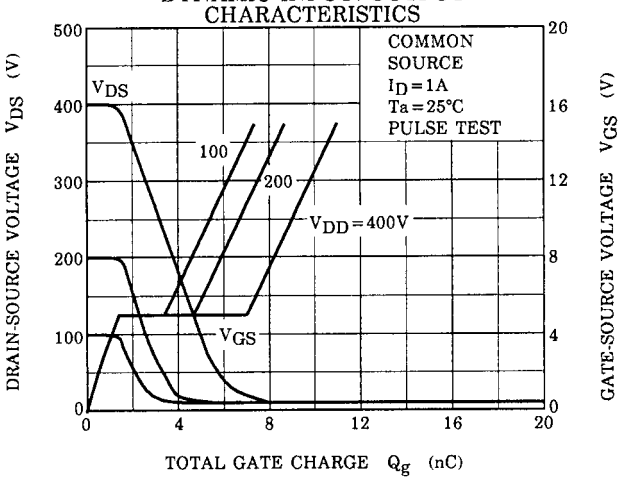
V_{th} – Ta

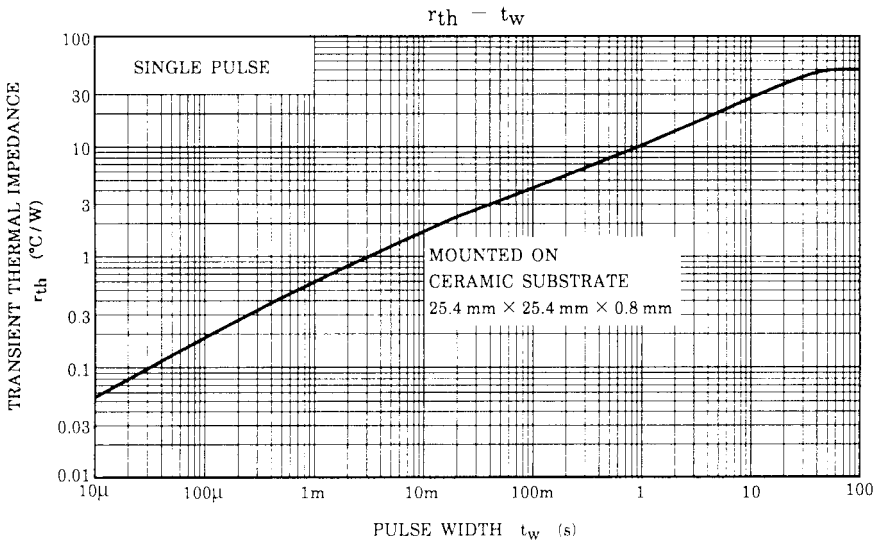


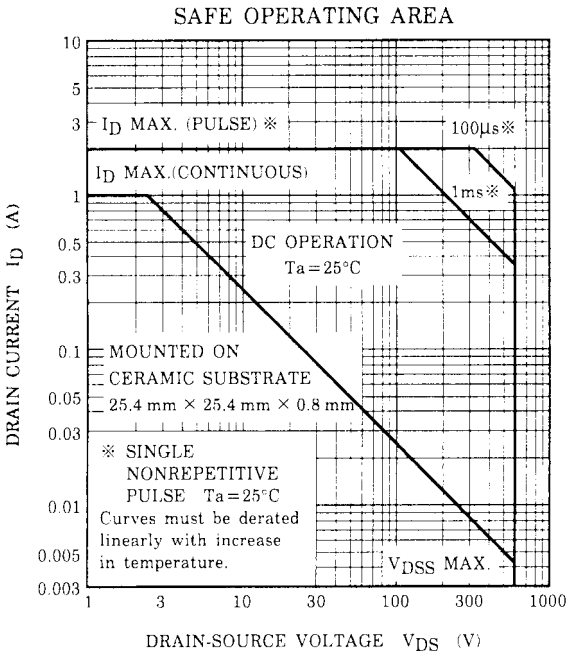
P_D – Ta

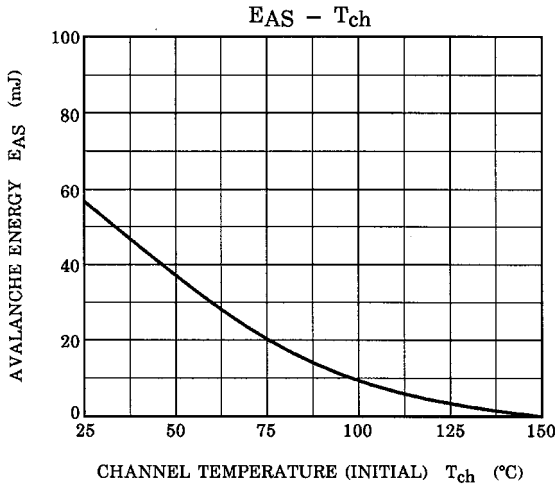


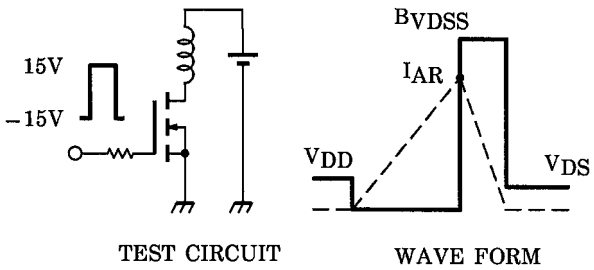
DYNAMIC INPUT / OUTPUT CHARACTERISTICS











$R_G = 25\ \Omega$
$V_{DD} = 90$ V, L = 100 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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